

Gallium Arsenide Schottky Rectifier

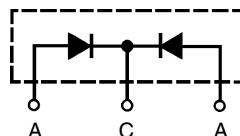
$$I_{FAV} = 2 \times 12 \text{ A}$$

$$V_{RRM} = 220/250 \text{ V}$$

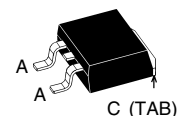
$$C_{Junction} = 18 \text{ pF}$$

Preliminary Data

V_{RSM} V	V_{RRM} V	Type
220	220	DGSK 20-022AS
250	250	DGSK 20-025AS



TO-263 AB



A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FAV}	$T_C = 25^\circ\text{C}$; DC	12	A
I_{FAV}	$T_C = 90^\circ\text{C}$; DC	9	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	20	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	34	W

Features

- Low forward voltage
- Very high switching speed
- Low junction capacity of GaAs
 - low reverse current peak at turn off
- Soft turn off
- Temperature independent switching behaviour
- High temperature operation capability
- Epoxy meets UL 94V-0

Applications

- MHz Switched mode power supplies (SMPs)
- Small size SMPs
- High frequency converters
- Resonant converters

Symbol	Conditions	Characteristic Values		
		typ.	max.	
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	1.3	1.3	mA mA
V_F	$I_F = 5 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 5 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	1.3 1.2	1.5	V V
C_J	$V_R = 100 \text{ V}$; $T_{VJ} = 125^\circ\text{C}$	18		pF
R_{thJC}			4.4	K/W
Weight		2		g

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

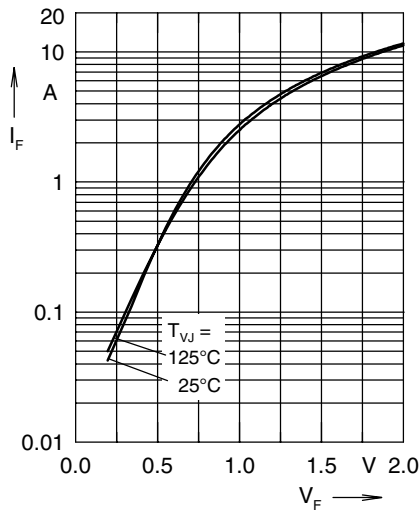


Fig. 1 typ. forward characteristics

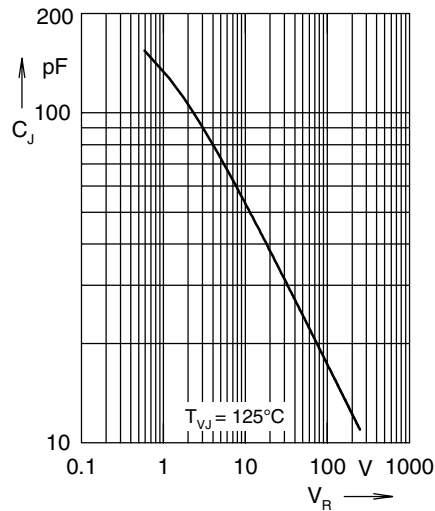


Fig. 2 typ. junction capacity
versus blocking voltage

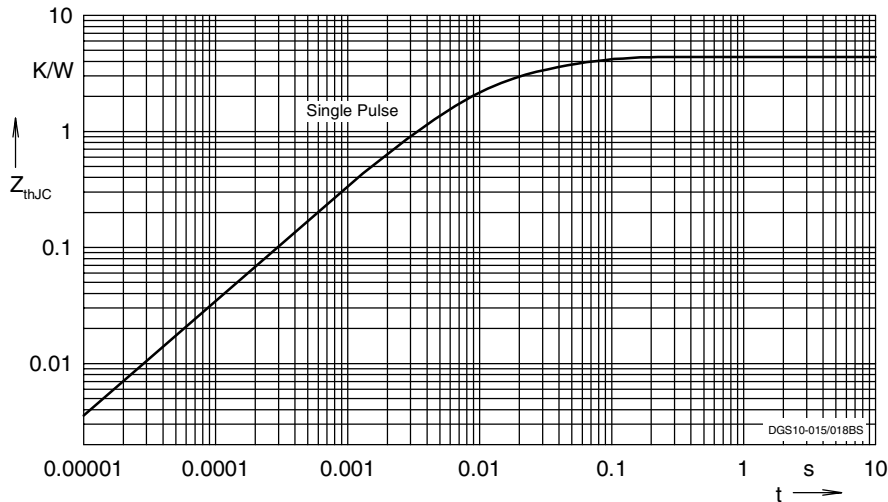
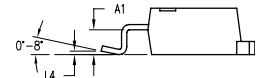
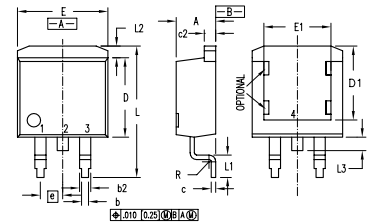


Fig. 3 typ. thermal impedance junction to case

Note:
explanatory comparison of the basic operational behaviour of rectifier diodes and Gallium Arsenide Schottky diodes:

	Rectifier Diode	GaAs Schottky Diode
conduction	by majority + minority carriers	by majority carriers only
forward characteristics	V_F (I_F)	V_F (I_F), see Fig. 1
turn off characteristics	extraction of excess carriers causes temperature dependant reverse recovery (t_{rr} , I_{RM} , Q_{rr})	reverse current charges junction capacity C_J , see Fig. 2; not temperature dependant
turn on characteristics	delayed saturation leads to V_{FR}	no turn on overvoltage peak

Outline TO-263 AB



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.315	.350
E	9.65	10.29	.380	.405
E1	6.22	8.13	.245	.320
e	2.54 BSC		.100 BSC	
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.20	0	.008
R	0.46	0.74	.018	.029